

HL6314MG/24MG

AlGaInP Laser Diodes

HITACHI

ADE-208-262D (Z)
5th Edition
Dec. 2000

Description

The HL6314MG/24MG are 0.63 μm band AlGaInP laser diodes with a multi-quantum well (MQW) structure. They are suitable as light sources for laser pointers and optical equipment for amusement.

Application

- Laser pointer

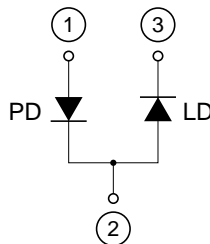
Features

- Visible light output: 635 nm Typ (nearly equal to He-Ne gas laser)
- Optical output power: 3 mW CW
- Low operating current: 30 mA Typ
- Low operating voltage: 2.7 V Max
- TM mode oscillation

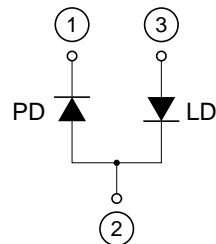
Package Type
• HL6314MG/24MG: MG



Internal Circuit
• HL6314MG



Internal Circuit
• HL6324MG



Absolute Maximum Ratings (T_C = 25°C)

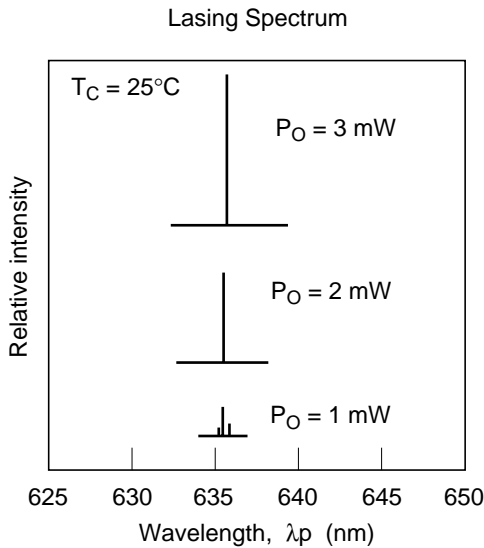
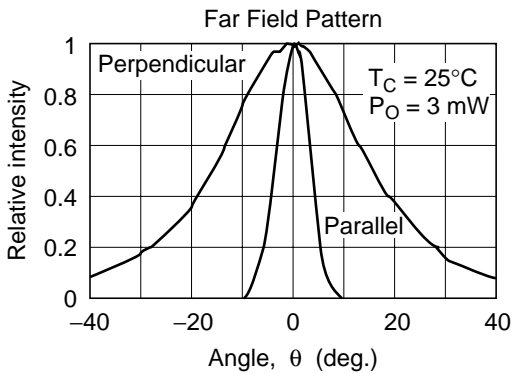
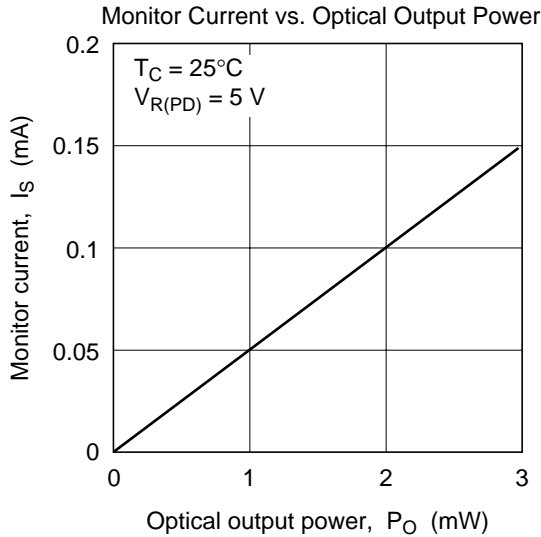
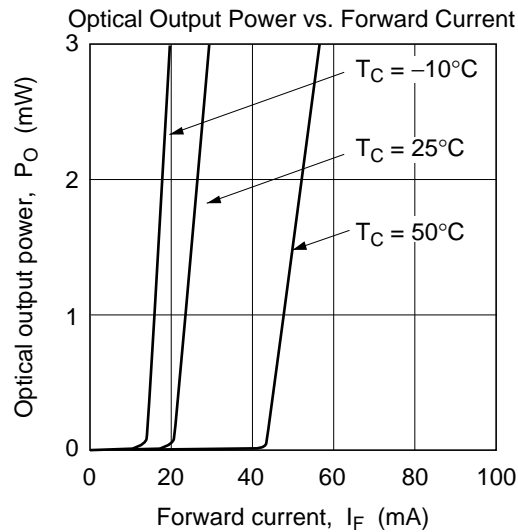
Item	Symbol	Rated Value	Unit
Optical output power	P _O	3	mW
Pulse optical output power	P _{O(pulse)}	5 *	mW
LD reverse voltage	V _{R(LD)}	2	V
PD reverse voltage	V _{R(PD)}	30	V
Operating temperature	Topr	−10 to +50	°C
Storage temperature	Tstg	−40 to +85	°C

Note: Pulse condition : Pulse width ≤ 1 μs , duty ≤ 50%

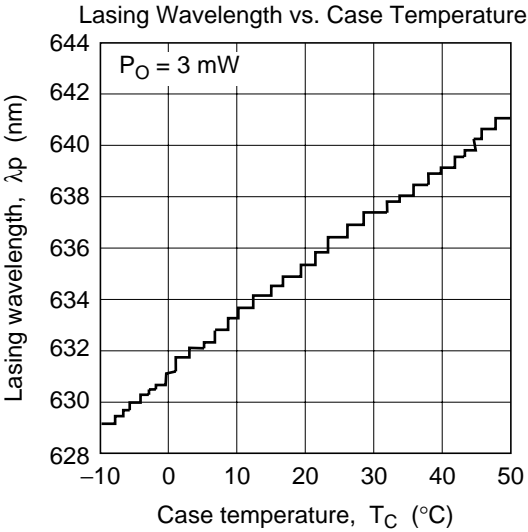
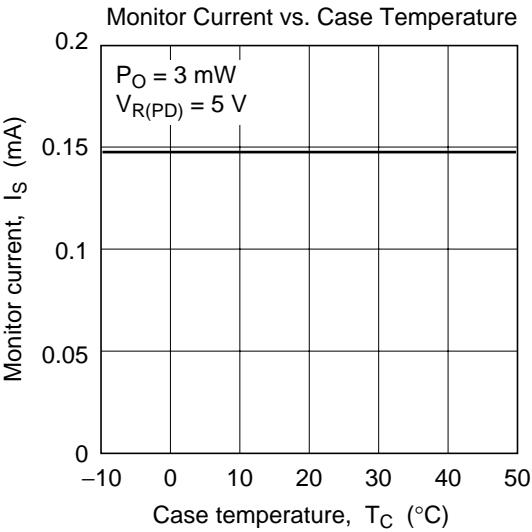
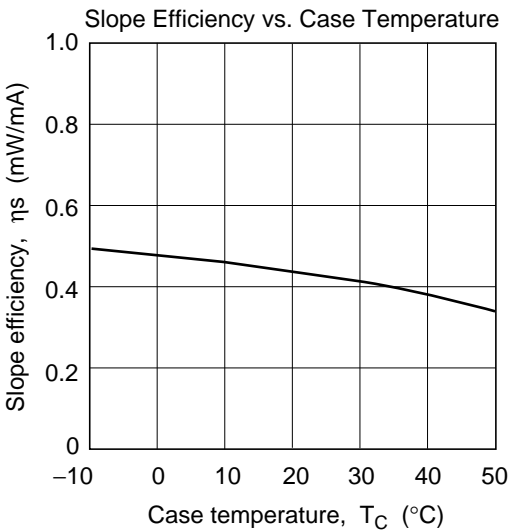
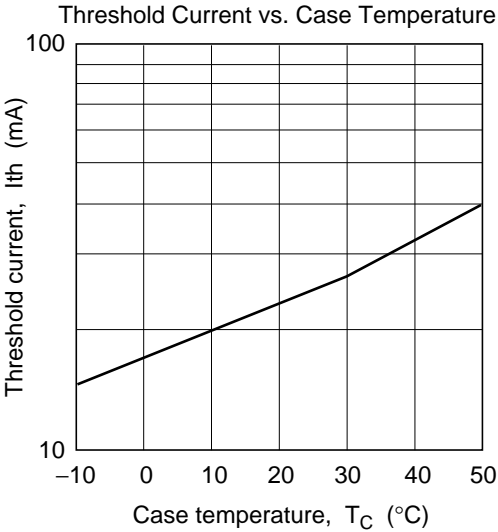
Optical and Electrical Characteristics (T_C = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical output power	P _O	3	—	—	mW	Kink free
Threshold current	I _{th}	—	25	35	mA	
Operating current	I _{OP}	—	30	42	mA	P _O = 3 mW
Operating voltage	V _{OP}	—	—	2.7	V	P _O = 3 mW
Beam divergence parallel to the junction	θ//	6	8	10	deg.	P _O = 3 mW
Beam divergence parpendicular to the junction	θ⊥	23	30	39	deg.	P _O = 3 mW
Astigmatism	A _s	—	8	—	μm	P _O = 3 mW, NA = 0.55
Lasing wavelength	λ _p	630	635	640	nm	P _O = 3 mW
Monitor current	I _s	0.08	0.15	0.40	mA	P _O = 3 mW, V _{R(PD)} = 5 V

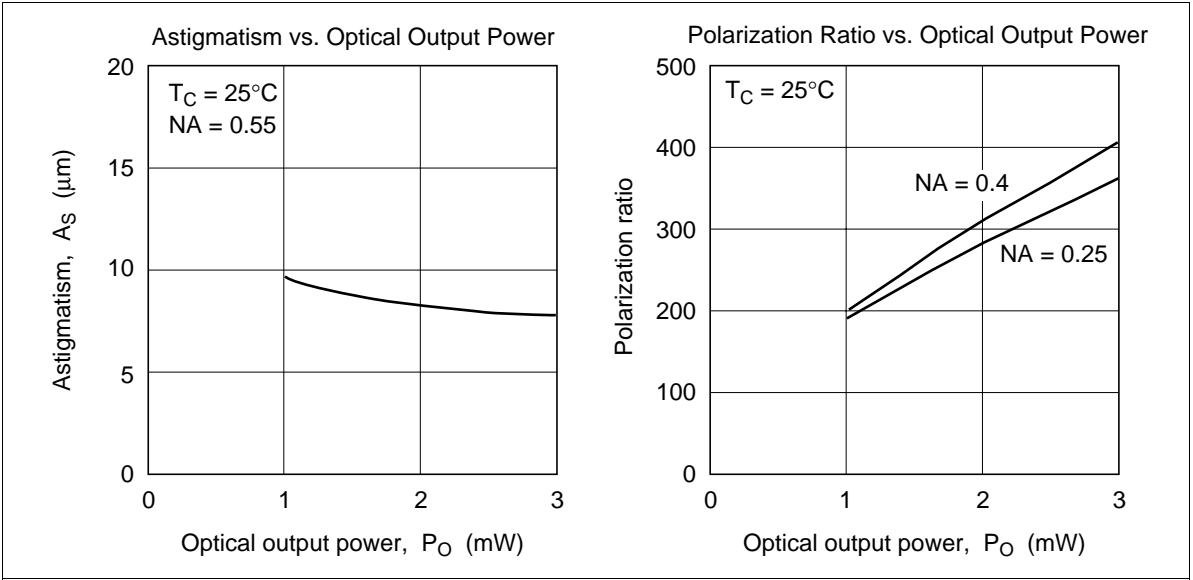
Typical Characteristic Curves



Typical Characteristic Curves (cont)



Typical Characteristic Curves (cont)



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1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.

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